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(54) **ORGANIC LIGHT EMITTING DIODE
DISPLAY**

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CPC **H01L 51/5209** (2013.01); **H01L 27/3216**
(2013.01); **H01L 27/3218** (2013.01); **H01L**
51/5268 (2013.01)

(58) **Field of Classification Search**

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27/3218; H01L 27/3216

See application file for complete search history.

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(57) **ABSTRACT**

An organic light emitting diode (OLED) display is disclosed. In one aspect, the OLED display includes a substrate, a plurality of transistors formed over the substrate and a passivation layer covering the transistors. The OLED display also includes an OLED formed over the passivation layer and including a pixel electrode, an organic emission layer, and a common electrode. The pixel electrode includes a first curved portion that does not overlap the organic emission layer in the depth dimension of the OLED display.

19 Claims, 9 Drawing Sheets

100

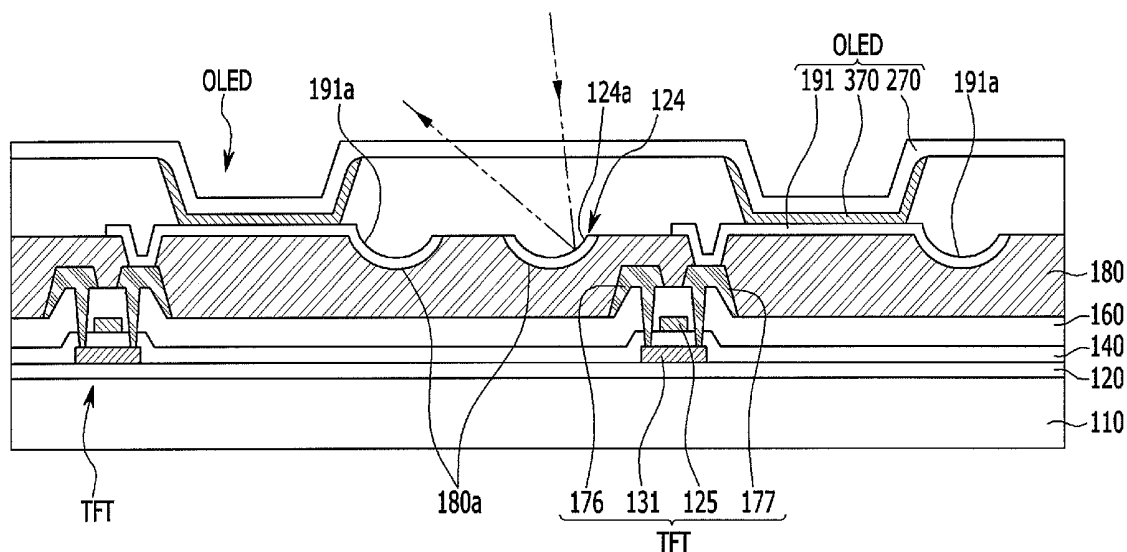


FIG. 1

100

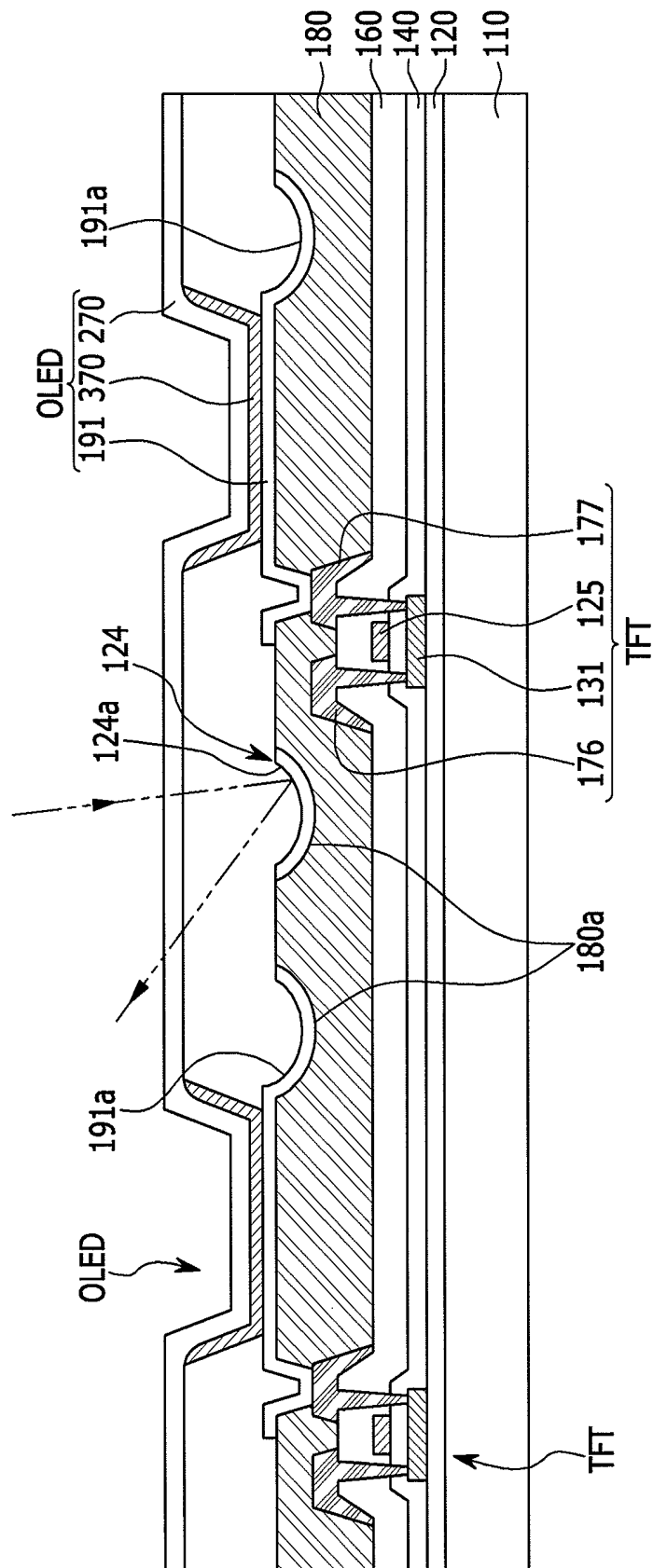


FIG. 2

101

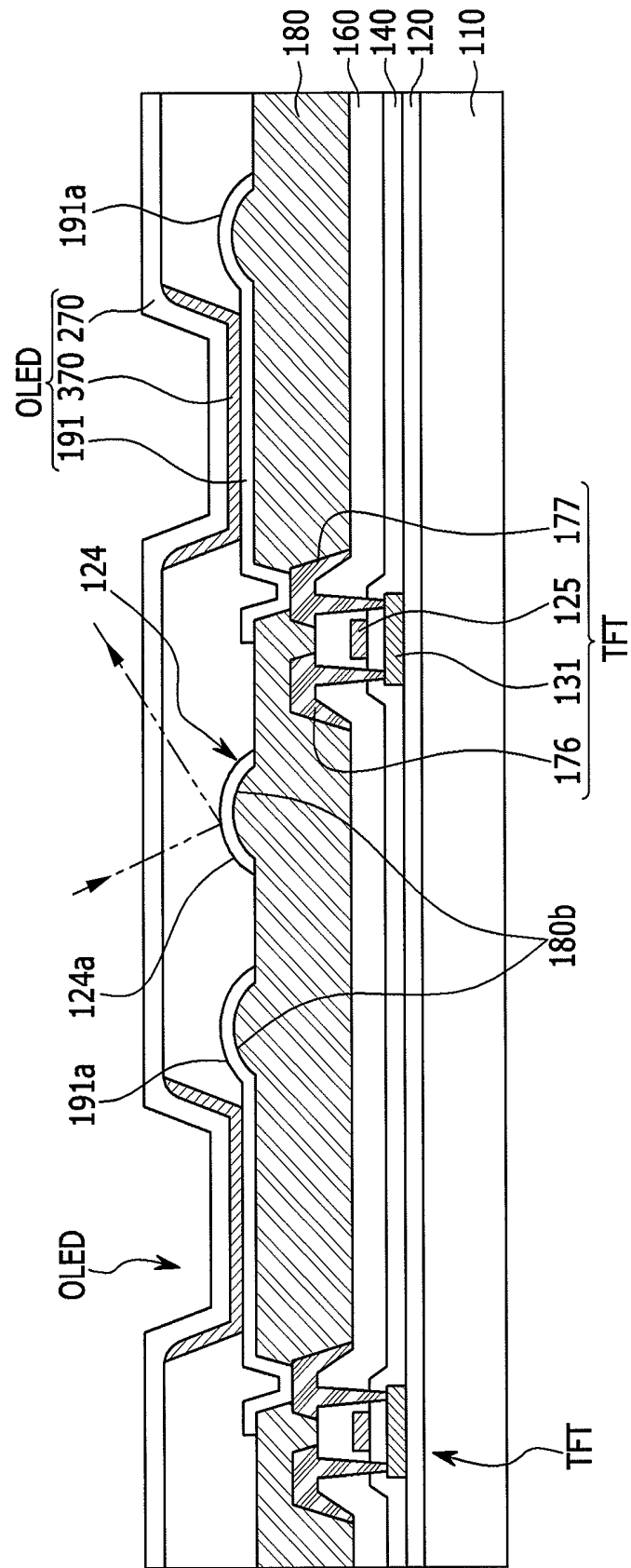


FIG. 3

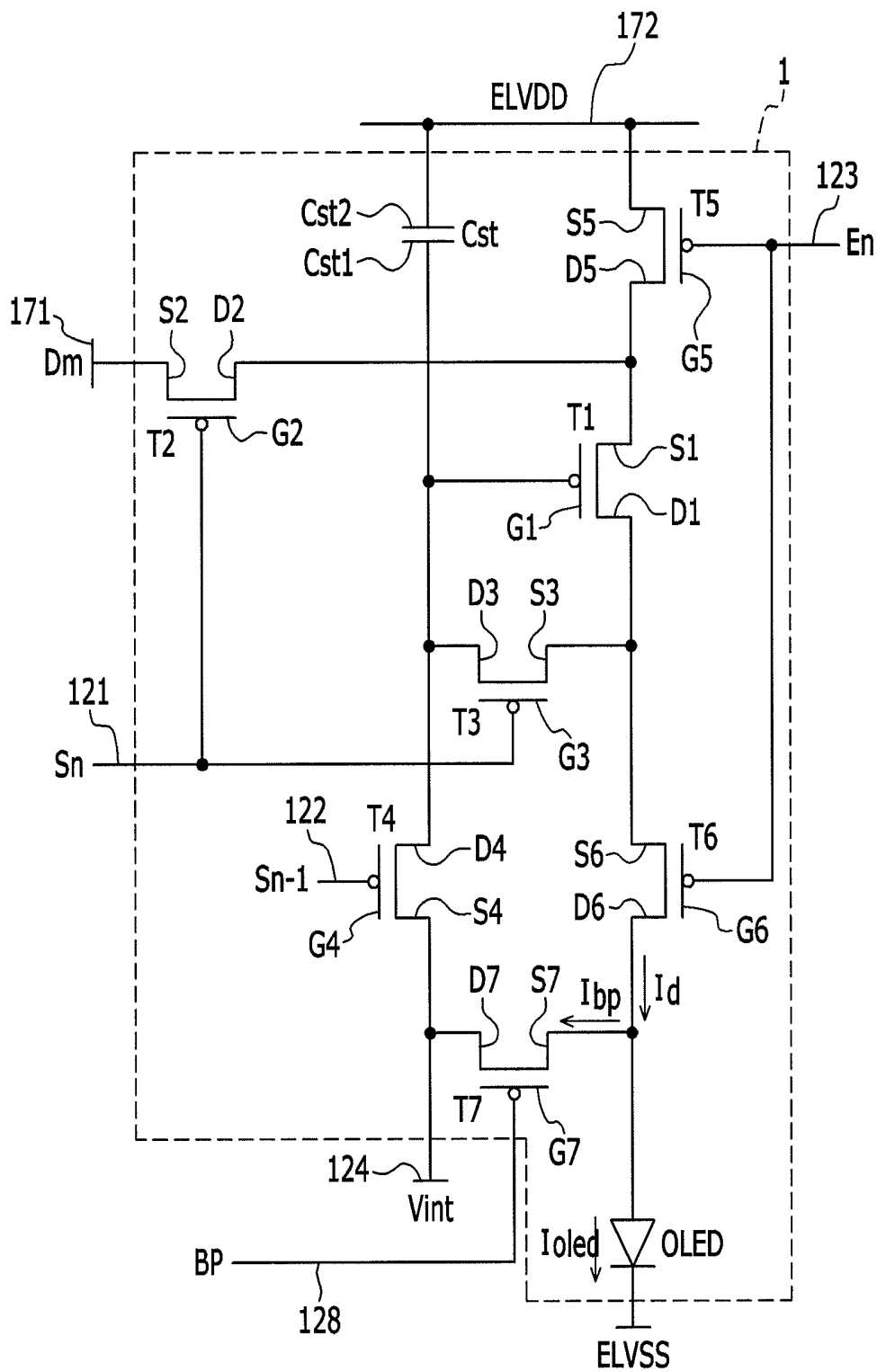


FIG. 4

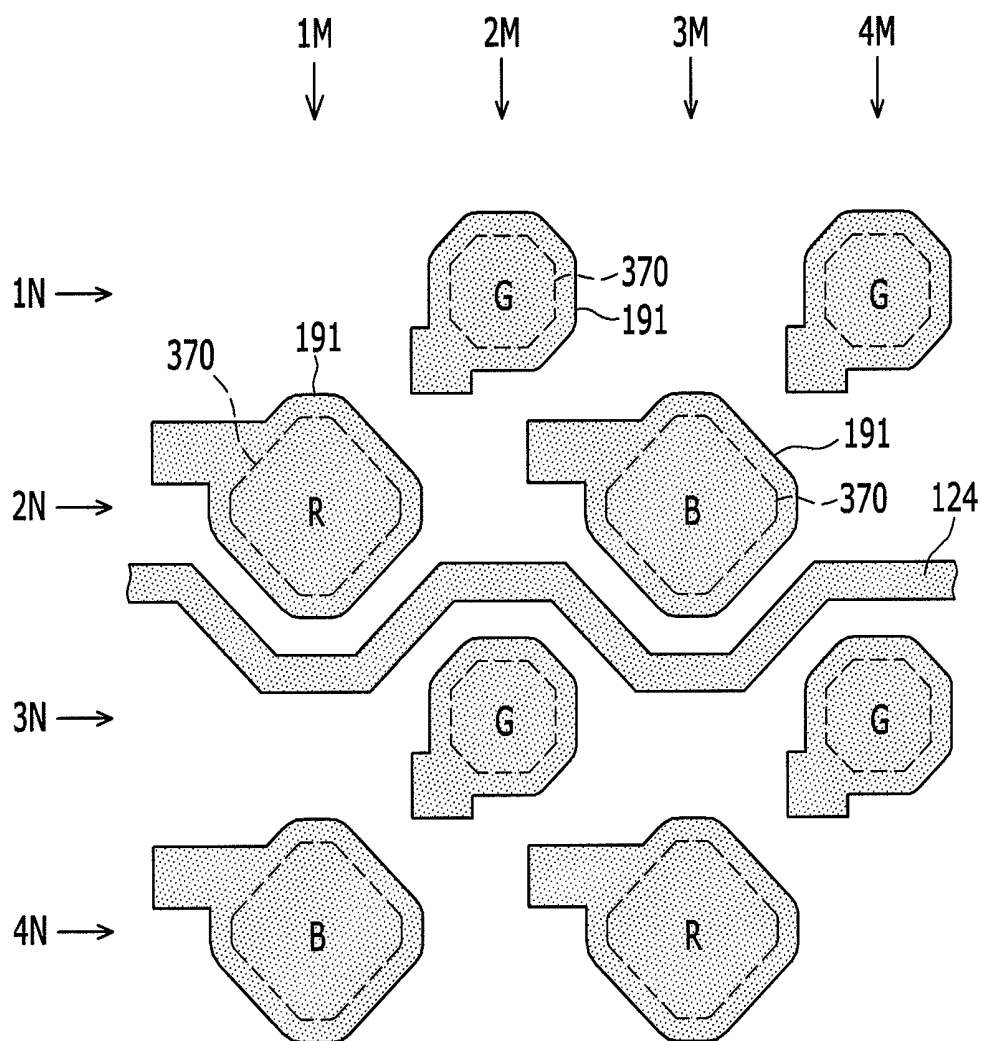


FIG. 5

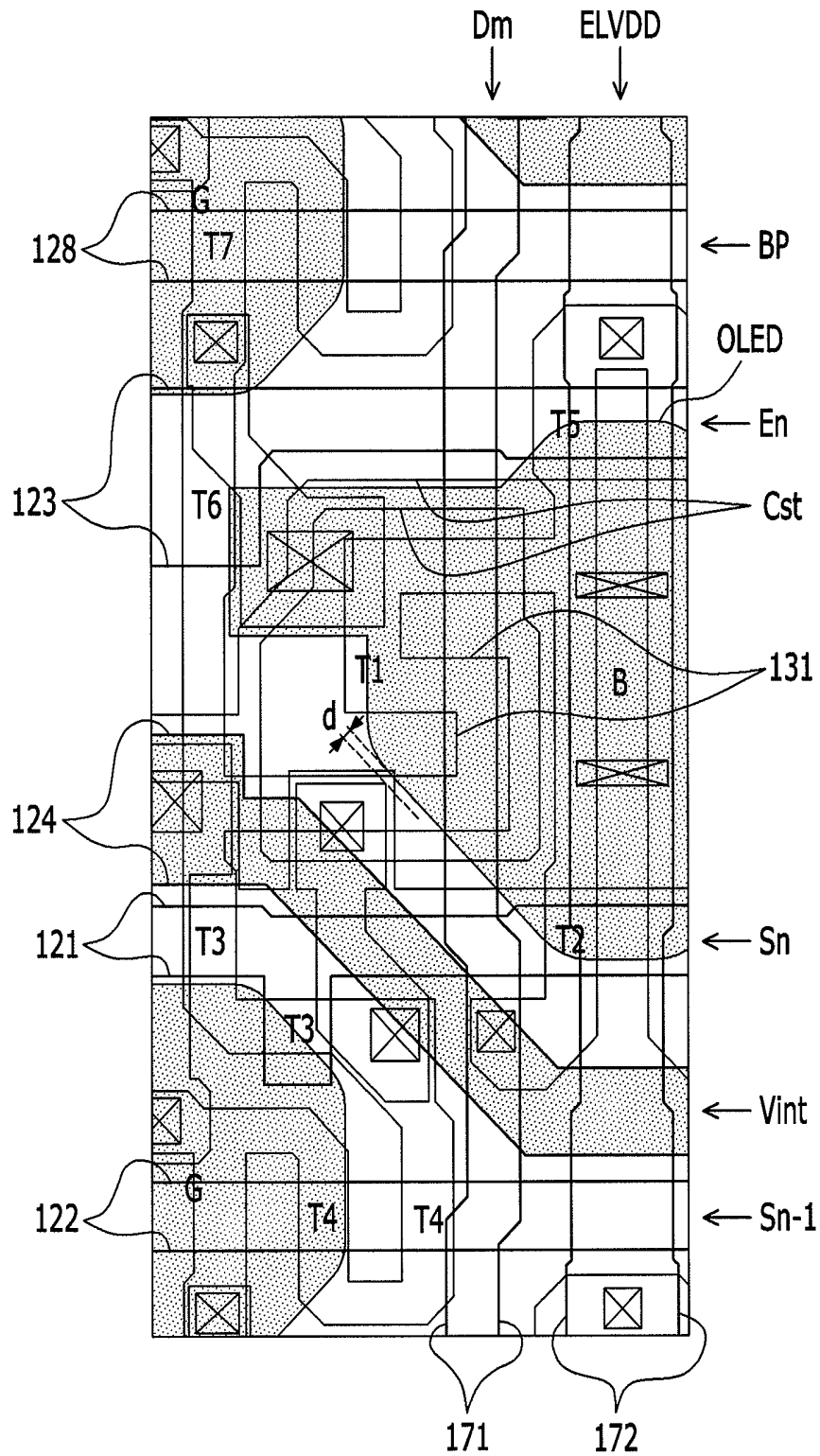


FIG. 6

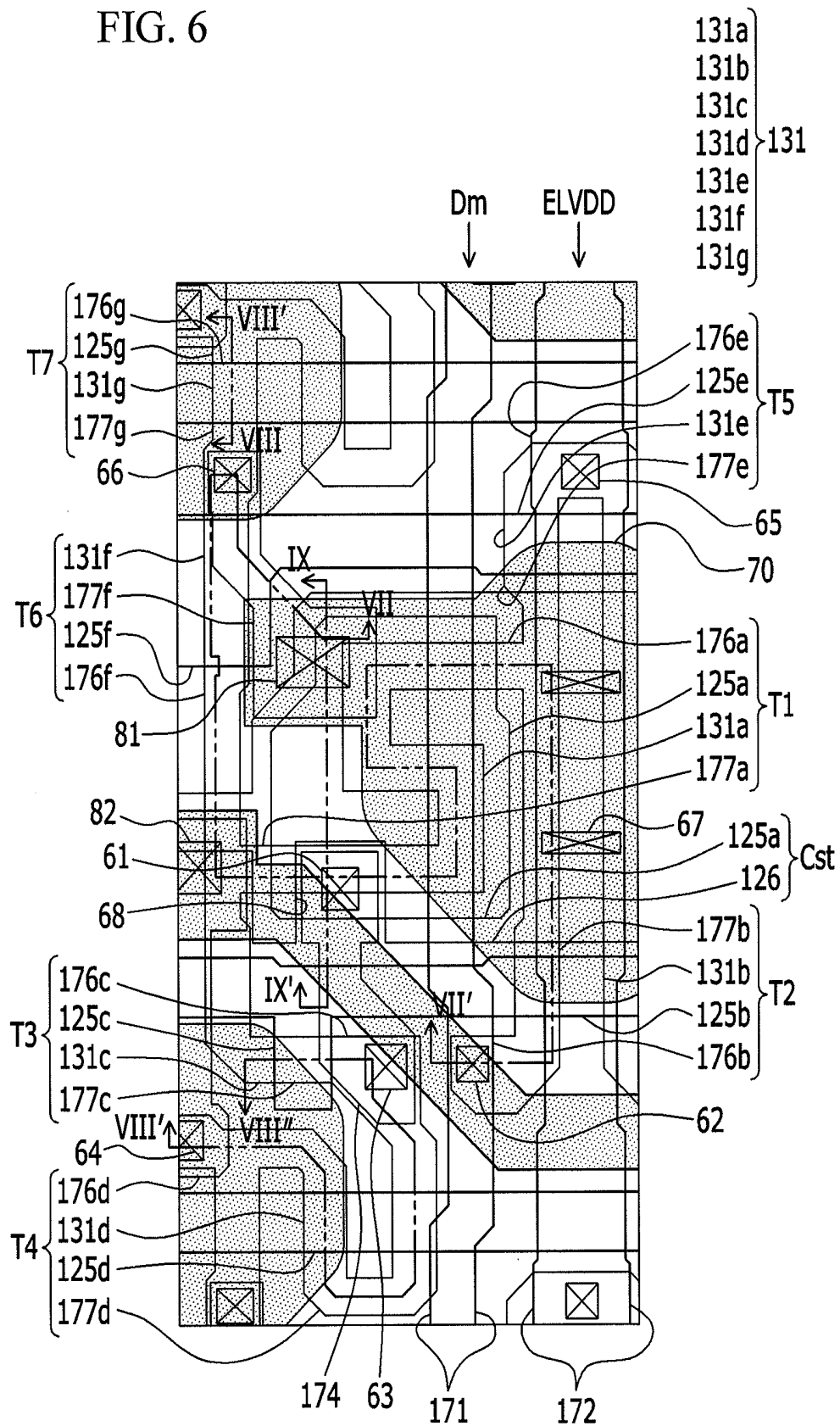


FIG. 7

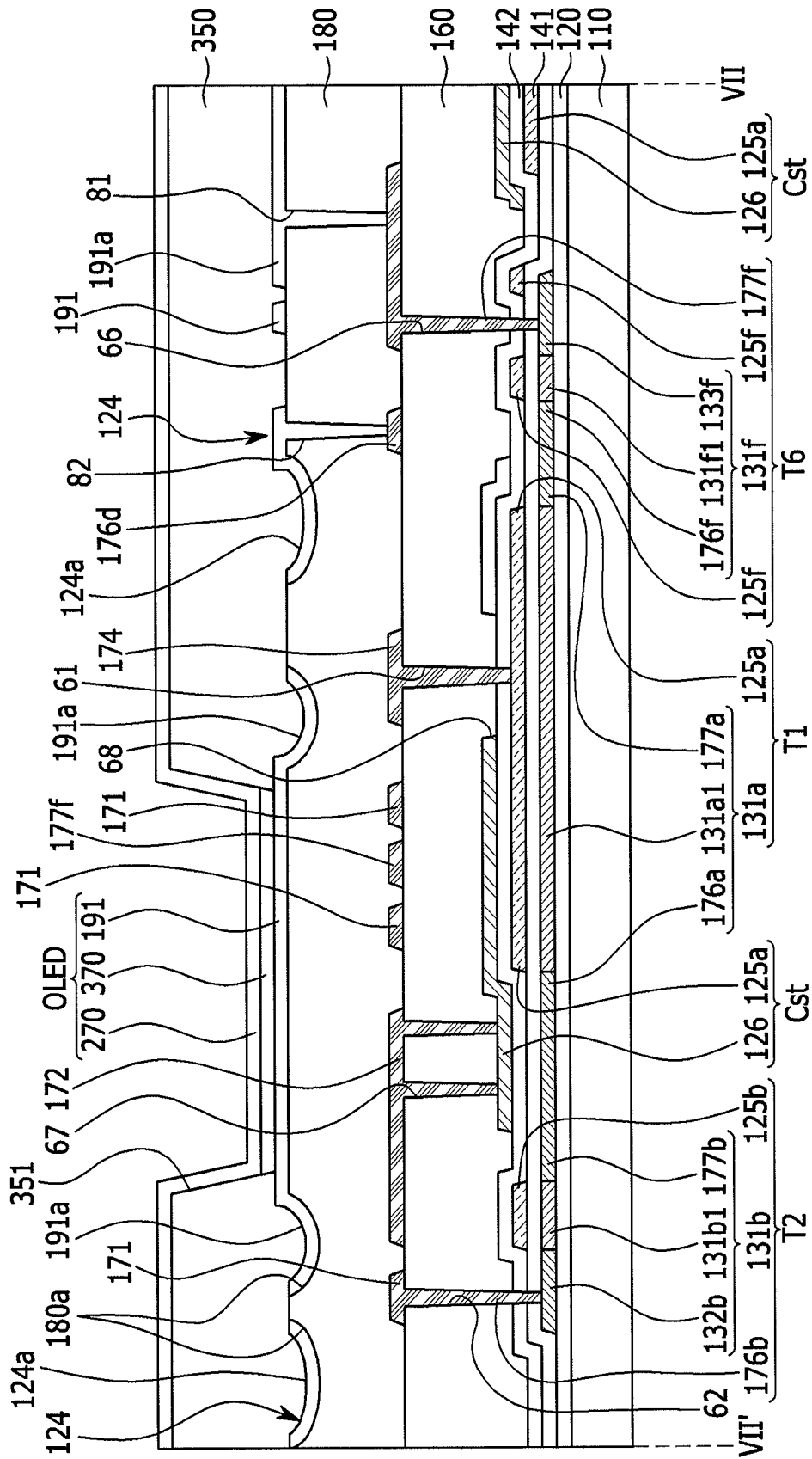


FIG. 8

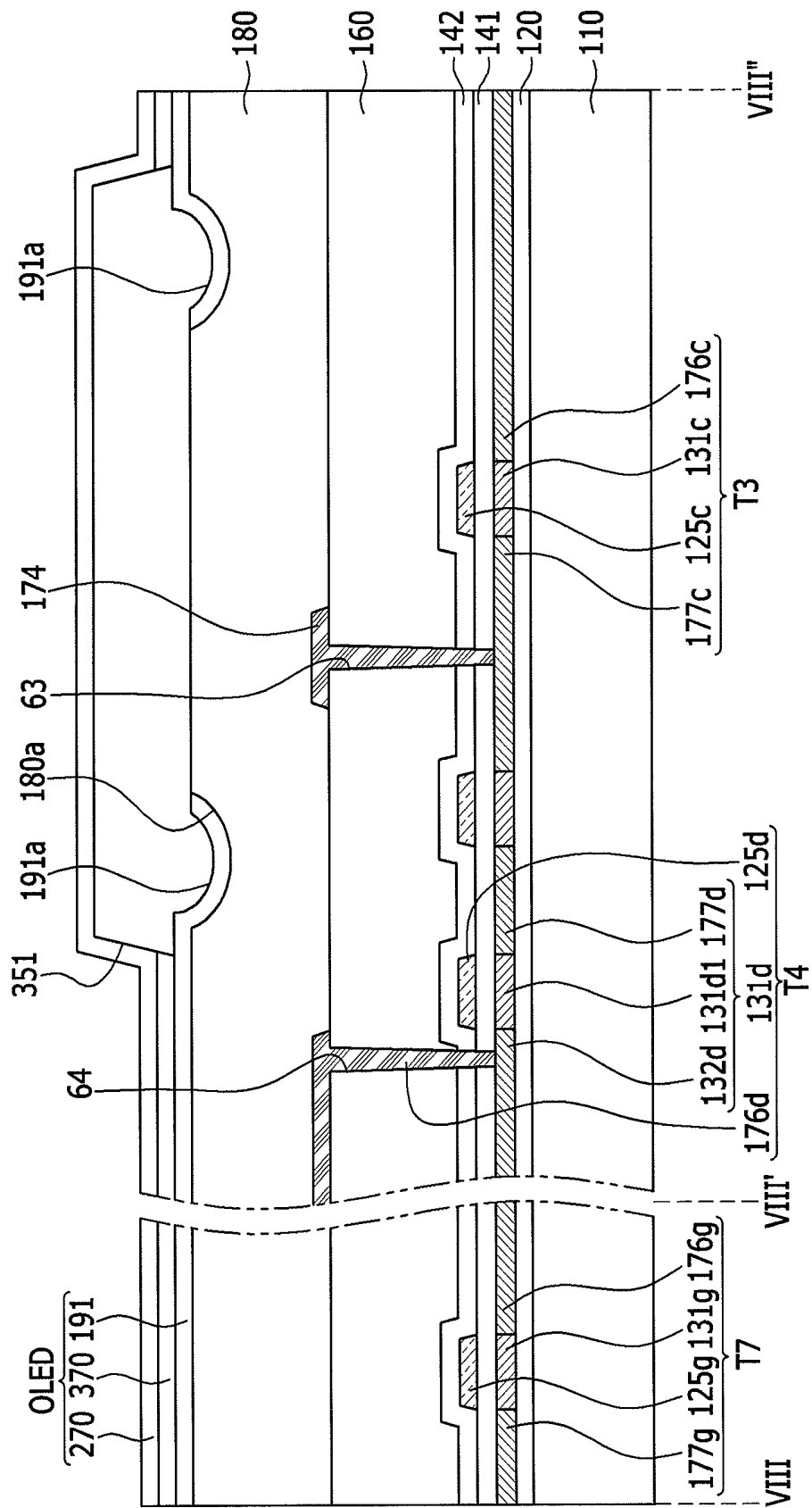
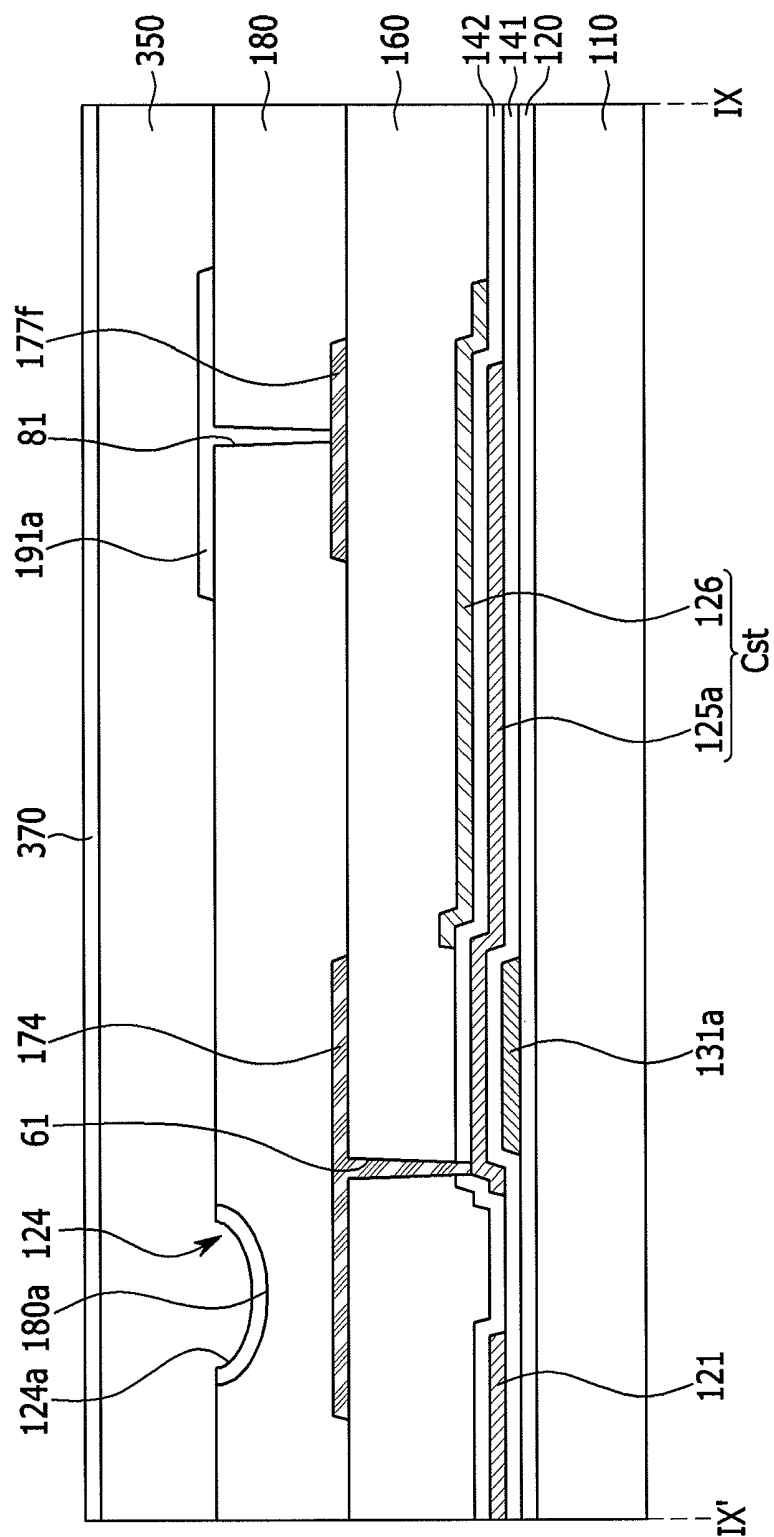


FIG. 9



ORGANIC LIGHT EMITTING DIODE DISPLAY

RELATED APPLICATIONS

This application claims priority to and the benefit of Korean Patent Application No. 10-2014-0169851 filed in the Korean Intellectual Property Office on Dec. 1, 2014, the entire contents of which are incorporated herein by reference.

BACKGROUND

Field

The described technology generally relates to an organic light emitting diode display.

Description of the Related Technology

An organic light emitting diode (OLED) display includes a matrix of OLEDs each configured by a hole injection electrode, an organic emission layer, and an electron injection electrode. An electron and a hole are coupled with each other in the organic emission layer to generate an exciton, and light is emitted by energy generated when the exciton falls from an excited state to a ground state. OLED technology displays a predetermined image by careful control of the emitted light.

One of the hole injection electrode and the electron injection electrode becomes a pixel electrode, and the other electrode becomes a common electrode. The pixel electrode and the organic emission layer are provided for each subpixel (a pixel includes multiple colors subpixels), and the pixel electrode is electrically connected with a thin film transistor of the corresponding subpixel. The common electrode is formed over the display area. The pixel may include a red subpixel, a green subpixel, and a blue subpixel, and further include a white subpixel.

SUMMARY OF CERTAIN INVENTIVE ASPECTS

One inventive aspect relates to an OLED display for enhanced visibility outdoors.

Another aspect is an OLED display capable of increasing outside visibility and a contrast ratio of a screen by minimizing reflection of external light by a metal reflective film such as a pixel electrode.

Another aspect is an OLED display including: a substrate; a plurality of transistors formed on the substrate; a passivation layer covering the transistors; and an OLED formed on the passivation layer and including a pixel electrode, an organic emission layer, and a common electrode. The pixel electrode may include a first curved portion positioned in a region which does not overlap with the organic emission layer.

The pixel electrode may include a metal reflective film, and the common electrode may include any one of a transparent conductive film and a translucent conductive film. The OLED display may further include an initialization voltage line formed on the passivation layer with the same material as the pixel electrode, in which the initialization voltage line may include a second curved portion.

The first curved portion and the second curved portion may be formed concavely toward the common electrode. The surface of the passivation layer may include a plurality of concave portions, and the first curved portion and the second curved portion may be formed on the concave portions with predetermined thicknesses.

On the other hand, the first curved portion and the second curved portion may be formed convexly toward the common electrode. The surface of the passivation layer may include a plurality of convex portions, and the first curved portion and the second curved portion may be formed on the convex portions with predetermined thicknesses.

The second curved portion may be formed at the remaining portion except for the portion overlapping with the contact hole of the initialization voltage line.

The curved portions formed on the pixel electrode and the initialization voltage line scatter external light to minimize reflection of the external light. According to the OLED display of the exemplary embodiment, it is possible to improve a contrast ratio of a screen and outside visibility by minimizing the reflection of the external light.

Another aspect is an organic light emitting diode (OLED) display, comprising: a substrate; a plurality of transistors formed over the substrate; a passivation layer covering the transistors; and an OLED formed over the passivation layer and including a pixel electrode, an organic emission layer, and a common electrode, wherein the pixel electrode includes a first curved portion that does not overlap the organic emission layer in the direction of light emission.

In the above display, the pixel electrode includes a metal reflective film, and wherein the common electrode includes at least one of a transparent conductive film and a translucent conductive film. The above display further comprises: an initialization voltage line formed over the passivation layer and formed of the same material as the pixel electrode, wherein the initialization voltage line includes a second curved portion.

In the above display, the first and second curved portions have substantially the same shape. In the above display, the first and second curved portions have substantially the same size. In the above display, the first and second curved portions do not directly contact each other. In the above display, neither of the first and second curved portions is formed directly above the transistors. In the above display, the first and second curved portions are concave toward the common electrode. In the above display, the surface of the passivation layer includes a plurality of concave portions, and wherein the first and second curved portions are formed over the concave portions with predetermined thicknesses. In the above display, the first and second curved portions are convex toward the common electrode.

In the above display, the surface of the passivation layer includes a plurality of convex portions, and wherein the first and second curved portions are formed over the convex portions with predetermined thicknesses. In the above display, the second curved portion is formed at the remaining portion except for the portion overlapping the contact hole of the initialization voltage line. In the above display, the first curved portion is not formed directly below the organic emission layer. In the above display, each of the transistors includes source and drain electrodes, wherein the pixel electrode includes a non-linear portion that contacts one of the source and drain electrodes, and wherein the height of the first curved portion is similar to that of the non-linear portion. In the above display, the passivation layer has a groove or protrusion on which the first curved portion is formed.

Another aspect is an organic light emitting diode (OLED) display, comprising: a substrate; a plurality of transistors formed over the substrate; a passivation layer covering the transistors; and a plurality of OLEDs formed over the passivation layer, wherein each of the OLEDs includes a pixel electrode, an organic emission layer, and a common

electrode, wherein the pixel electrode includes at least one first curved portion that is convex or concave with respect to the common electrode, and wherein the first curved portion is formed between adjacent organic emission layers.

In the above display, the first curved portion does not overlap the organic emission layer in the depth dimension of the OLED display. The above display further comprises an initialization voltage line formed over the passivation layer, wherein the initialization voltage line includes at least one second curved portion that is convex or concave with respect to the common electrode. In the above display, the passivation layer has a groove or protrusion on which the first curved portion is formed. In the above display, the first curved portion is not formed directly above any of the transistors.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a partially enlarged cross-sectional view of an OLED display according to an exemplary embodiment.

FIG. 2 is a partially enlarged cross-sectional view of an OLED display according to another exemplary embodiment.

FIG. 3 is an equivalent circuit diagram of one pixel of the OLED display according to the exemplary embodiment.

FIG. 4 is a schematic layout view of a plurality of pixels of the organic light emitting display according to the exemplary embodiment.

FIG. 5 is a schematic plan view illustrating a plurality of transistors and a plurality of signal lines of the organic light emitting display according to the exemplary embodiment.

FIG. 6 is a detailed layout view of FIG. 5.

FIG. 7 is a cross-sectional view taken along line VII-VII' of FIG. 6.

FIG. 8 is a cross-sectional view taken along lines VIII-VIII' and VIII'-VIII'' of FIG. 6.

FIG. 9 is a cross-sectional view taken along line IX-IX' of FIG. 6.

DETAILED DESCRIPTION OF CERTAIN INVENTIVE EMBODIMENTS

For a front emission type OLED display, the pixel electrode is formed as a metal reflective layer and the common electrode is formed as a transparent conductive film or a translucent conductive film. Light emitted from the organic emission layer is reflected from the pixel electrode and passes through the common electrode to be displayed. However, when the OLED display is observed from the environment, external light is reflected by the pixel electrode to decrease a contrast ratio of a screen and outside visibility.

The present disclosure will be described more fully hereinafter with reference to the accompanying drawings, in which exemplary embodiments of the disclosure are shown. As those skilled in the art would realize, the described embodiments may be modified in various different ways, all without departing from the spirit or scope of the present disclosure.

It will be understood that when an element such as a layer, film, region, or substrate is referred to as being "on" another element, it can be directly on the other element or intervening elements may also be present. Further, in the specification, the word "on" means positioning on or below the object portion, but does not essentially mean positioning on the upper side of the object portion based on a gravity direction.

In addition, the size and thickness of each configuration shown in the drawings may be arbitrarily shown for understanding and ease of description, but the present disclosure

is not limited thereto. In this disclosure, the term "substantially" includes the meanings of completely, almost completely or to any significant degree under some applications and in accordance with those skilled in the art. Moreover, "formed on" can also mean "formed over." The term "connected" includes an electrical connection.

FIG. 1 is a partially enlarged cross-sectional view of an OLED display according to an exemplary embodiment.

Referring to FIG. 1, an OLED display 100 includes a substrate 110, a thin film transistor TFT formed on the substrate 110, a passivation layer 180 covering the thin film transistor TFT, and an OLED formed on the passivation layer 180.

The substrate 110 can be a rigid substrate such as glass, quartz, and metal, or a flexible substrate such as a plastic film. In the case of the flexible substrate, the substrate 110 may be made of polymer materials having excellent heat resistance and durability such as polyimide and polycarbonate.

A buffer layer 120 may be formed on the substrate 110. The buffer layer 120 serves to prevent an impurity from penetrating through the substrate 110 and provide a flat surface to the top of the substrate 110. The buffer layer 120 may include an inorganic material such as SiO₂ and SiN_x or an organic material such as polyimide, polyester, and acryl.

The thin film transistor TFT is formed on the buffer layer 120. The thin film transistor TFT includes a semiconductor layer 131, a gate electrode 125, a source electrode 176, and a drain electrode 177. The semiconductor layer 131 may be made of polysilicon or oxide semiconductors, and in the case of the oxide semiconductor, a separated passivation layer may be added onto the semiconductor layer 131. The semiconductor layer 131 includes a channel region, and a source region and a drain region which are positioned at both sides of the channel region and doped with impurities.

A gate insulating layer 140 is formed on the semiconductor layer 131. The gate insulating layer 140 is to insulate the semiconductor layer 131 and the gate electrode 125 from each other and may include an inorganic material such as SiO₂ and SiN_x or an organic material. The gate electrode 125 is formed on the gate insulating layer 140. The gate electrode 125 at least partially overlaps the channel region of the semiconductor layer 131 and may include Au, Ag, Cu, Ni, Pt, Pd, Al, Mo, or the like.

An interlayer insulating layer 160 is formed on the gate electrode 125. The interlayer insulating layers 160 are disposed between the gate electrode 125 and the source electrode 176 and between the gate electrode 125 and the drain electrode 177 to insulate them from each other. The interlayer insulating layer 160 can include an inorganic material such as SiO₂ and SiN_x and may have a double-layer structure of a SiO₂ layer and a SiN_x layer.

The source electrode 176 and the drain electrode 177 are formed on the interlayer insulating layer 160. In this case, contact holes are formed in the interlayer insulating layer 160 and the gate insulating layer 140 to expose the source region and the drain region of the semiconductor layer 131, and through the contact holes, the source electrode 176 contacts the source region and the drain electrode 177 contacts the drain region.

In FIG. 1, a top gate type thin film transistor TFT is illustrated as an example, but a structure of the thin film transistor TFT is not limited to the illustrated example. The thin film transistor TFT is covered and protected by the passivation layer 180 and electrically connected to the OLED to drive the OLED.

The passivation layer **180** is formed by an inorganic insulating layer or an organic insulating layer, or may be formed by a laminated structure of the inorganic insulating layer and the organic insulating layer. The inorganic insulating layer may include SiO₂, SiNx, Al₂O₃, TiO₂, Ta₂O₅, HfO₂, ZrO₂, or the like, and the organic insulating layer may include polymethylmetacrylate (PMMA), polystyrene (PS), an acryl-based polymer, an imide-based polymer, an arylether-based polymer, or the like.

The OLED is formed on the passivation layer **180**, and includes a pixel electrode **191**, an organic emission layer **370**, and a common electrode **270**. One pixel electrode **191** is provided for each pixel and contacts the drain electrode **177** through the contact hole formed in the passivation layer **180**. The common electrode **270** can be formed on the entire display area. The organic emission layer **370** includes a light emission layer, and may include at least one of a hole injection layer, a hole transport layer, an electron transport layer, and an electron injection layer.

One of the pixel electrode **191** and the common electrode **270** serves as an anode injecting a hole to the organic emission layer **370**, and the other electrode serves as a cathode injecting an electron. The hole and the electron are coupled with each other in the organic emission layer **370** to generate an exciton, and light is emitted by energy generated when the exciton falls from an excited state to a ground state.

When the OLED display **100** is a front emission type, the pixel electrode **191** is formed as a metal reflective film, and the common electrode **270** is formed as a transparent conductive film or a translucent conductive film. The light emitted from the organic emission layer **370** is reflected from the pixel electrode **191** and passes through the common electrode **270** to be emitted to the outside.

The metal reflective film may include Au, Ag, Mg, Al, Pt, Pd, Ni, Nd, Ir, Cr, or the like. The transparent conductive film may include indium tin oxide (ITO), indium zinc oxide (IZO), ZnO, In₂O₃, or the like. The translucent conductive film may be formed as a metal thin film including Li, Ca, LiF/Ca, LiF/Al, Al, Ag, Mg, or the like, and a transparent film such as ITO, IZO, ZnO, In₂O₃ may be laminated on the translucent conductive film.

A capping layer (not illustrated) may be formed on the common electrode **270**. The capping layer serves to protect the OLED and optimize light efficiency through refractive index matching in the case of the front emission type. The capping layer may include an organic material such as α -NPD, NPB, TPD, m-MTDATA, Alq₃, or CuPc.

A blocking film (not illustrated) may be formed on the capping layer. The blocking layer may include an inorganic material such as LiF, MgF₂, CaF₂, or the like and prevent the OLED from being damaged by plasma used in a process of forming an inorganic film of thin film encapsulation. Further, the blocking layer may have a function of optimizing light efficiency by matching a refractive index in the case of the front emission type, like the capping layer.

An encapsulation part (not illustrated) sealing the OLED is formed on the blocking layer. The encapsulation part may be configured by a thin film encapsulation including at least a first inorganic film, a first organic film, and a second inorganic film. Since the OLED easily deteriorates by environmental moisture or oxygen, the thin film encapsulation seals the OLED to block contact with ambient conditions.

Meanwhile, the OLED display **100** may further include an initialization voltage line **124** transferring an initialization voltage. The initialization voltage line **124** may be formed of a material (metal reflective film) such as the pixel electrode **191** on the passivation layer **180**.

In the first exemplary embodiment, the pixel electrode **191** includes a first curved portion **191a** positioned in a region which does not overlap or is not formed directly below the organic emission layer **370**. The first curved portion **191a** may be an edge region of the pixel electrode **191** surrounding the organic emission layer **370**. In addition, the initialization voltage line **124** includes a second curved portion **124a**. Here, the first curved portion **191a** and the second curved portion **124a** have curved shapes observed from the cross section and may be formed concavely toward the common electrode **270**. Each of the first and second curved portions **191a** and **124a** can be non-linear. The first and second curved portions **191a** and **124a** can have substantially the same shape and/or the same size. The height of each of the first and second curved portions **191a** and **124a** can be substantially the same or similar to that of the non-linear portion of the pixel electrode **191** that contacts the drain electrode **177** (see, e.g., FIG. 1). The height of each of the first and second curved portions **191a** and **124a** can be similar to or less than about half the height of the passivation layer **180**. The first and second curved portions **191a** and **124a** may not directly contact each other. Two or more first curved portions can be formed in the pixel electrode **191**. Furthermore, two or more second curved portions can be formed in the initialization voltage line **124**.

The surface of the passivation layer **180** is patterned to form a plurality of concave portions **180a** in a region where the edge of the pixel electrode **191** and the initialization voltage line **124** are to be positioned. In addition, the first curved portion **191a** of the pixel electrode **191** and the second curved portion **124a** of the initialization voltage line **124** may be formed on the concave portions **180a** with predetermined thicknesses.

The first curved portion **191a** of the pixel electrode **191** and the second curved portion **124a** of the initialization voltage line **124** do not directly reflect light (external light) incident from the environment but scatter the light to minimize reflection of external light. Accordingly, the OLED display **100** of the first exemplary embodiment may increase a contrast ratio and outside visibility.

FIG. 2 is a partially enlarged cross-sectional view of an OLED display according to another exemplary embodiment.

Referring to FIG. 2, an OLED display **101** is formed by the same configuration as the first exemplary embodiment described above, except that the first curved portion **191a** of the pixel electrode **191** and the second curved portion **124a** of the initialization voltage line **124** are formed convexly toward the common electrode **270**. The same members as the first exemplary embodiment use like reference numerals, and the duplicated description is omitted.

The surface of the passivation layer **180** is patterned to form a plurality of convex portions **180b** in a region where the edge of the pixel electrode **191** and the initialization voltage line **124** are to be positioned. In addition, the first curved portion **191a** of the pixel electrode **191** and the second curved portion **124a** of the initialization voltage line **124** may be formed on the convex portions **180b** with predetermined thicknesses.

The first curved portion **191a** of the pixel electrode **191** and the second curved portion **124a** of the initialization voltage line **124** do not directly reflect light (external light) incident from the environment but scatter the light to minimize reflection of external light. Accordingly, the OLED display **101** of the second exemplary embodiment may also increase contrast ratio and outdoor usage.

The OLED displays **100** and **101** of the first and second exemplary embodiments may include pentile matrix type

pixel structures, and rendering driving in which colors are expressed by sharing adjacent pixels may be applied. The OLED displays 100 and 101 may implement a high resolution with a small number of pixels. Next, the pentile matrix type pixel structure will be described in detail.

FIG. 3 is an equivalent circuit diagram of one pixel of the OLED display according to the exemplary embodiment.

Referring to FIG. 3, a pixel 1 of the OLED display includes a plurality of signal lines 121, 122, 123, 124, 128, 171, and 172, a plurality of transistors T1, T2, T3, T4, T5, T6, and T7 connected to the signal lines, a storage capacitor Cst, and an OLED.

The transistors may include a driving transistor T1, a switching transistor T2, a compensation transistor T3, an initialization transistor T4, an operation control transistor T5, a light emission control transistor T6, and a bypass transistor T7. The signal lines may include a scan line 121, a previous scan line 122, a light emission control line 123, an initialization voltage line 124, a bypass control line 128, a data line 171, and a driving voltage line 172.

The scan line 121 transfers a scan signal Sn, and the previous scan line 122 transfers a previous scan signal Sn-1 to the initialization transistor T4. The light emission control line 123 transfers a light emission control signal En to the operation control transistor T5 and the light emission control transistor T6. The initialization voltage line 124 transfers an initialization voltage Vint initializing the driving transistor T1, and the bypass control line 128 transfers a bypass signal BP to the bypass transistor T7. The data line 171 crosses the scan line 121 and transfers a data signal Dm. The driving voltage line 172 is formed substantially in parallel with the data line 171 and transfers a driving voltage ELVDD.

A gate electrode G1 of the driving transistor T1 is connected with one end Cst1 of the storage capacitor Cst, and the source electrode S1 of the driving transistor T1 is connected with the driving voltage line 172 via the operation control transistor T5. The drain electrode D1 of the driving transistor T1 is electrically connected with an anode of the OLED via the light emission control transistor T6. The driving transistor T1 receives the data signal Dm according to a switching operation of the switching transistor T2 to supply a driving current Id to the OLED.

A gate electrode G2 of the switching transistor T2 is connected with the scan line 121 and a source electrode S2 of the switching transistor T2 is connected with the data line 171. A drain electrode D2 of the switching transistor T2 is connected with the source electrode S1 of the driving transistor T1 and connected with the driving voltage line 172 via the operation control transistor T5. The switching transistor T2 is turned on according to the scan signal Sn received through the scan line 121 to perform a switching operation of transferring the data signal Dm transferred to the data line 171 to the source electrode S1 of the driving transistor T1.

A gate electrode G3 of the compensation transistor T3 is directly connected with the scan line 121. A source electrode S3 of the compensation transistor T3 is connected with the drain electrode D1 of the driving transistor T1 and connected with the anode of the OLED via the light emission control transistor T6. A drain electrode D3 of the compensation transistor T3 is connected to one end Cst1 of the storage capacitor Cst, a drain electrode D4 of the initialization transistor T4, and the gate electrode G1 of the driving transistor T1. The compensation transistor T3 is turned on according to the scan signal Sn received through the scan

line 121 and connects the gate electrode G1 and the drain electrode D1 of the driving transistor T1 to diode-connect the driving transistor T1.

A gate electrode G4 of the initialization transistor T4 is connected with the previous scan line 122 and a source electrode S4 of the initialization transistor T4 is connected with the initialization voltage line 124. A drain electrode D4 of the initialization transistor T4 is connected to one end Cst1 of the storage capacitor Cst, a drain electrode D3 of the compensation transistor T3, and the gate electrode G1 of the driving transistor T1. The initialization transistor T4 is turned on according to the previous scan signal Sn-1 received through the previous scan line 122 and transfers the initialization voltage Vint to the gate electrode G1 of the driving transistor T1 to perform an initialization operation of initializing a voltage of the gate electrode G1 of the driving transistor T1.

A gate electrode G5 of the operation control transistor T5 is connected with the light emission control line 123, and a source electrode S5 of the operation control transistor T5 is connected to the driving voltage line 172. A drain electrode D5 of the operation control transistor T5 is connected to the source electrode S1 of the driving transistor T1 and the drain electrode D2 of the switching transistor T2.

A gate electrode G6 of the light emission control transistor T6 is connected with the light emission control line 123, a source electrode S6 of the light emission control transistor T6 is connected with the drain electrode D1 of the driving transistor T1 and the source electrode S3 of the compensation transistor T3. A drain electrode D6 of the light emission control transistor T6 is electrically connected with the anode of the OLED. The operation control transistor T5 and the light emission control transistor T6 are simultaneously turned on according to the light emission control signal En received through the light emission control line 123, the driving voltage ELVDD is transferred to the OLED, and then a light emission current Ioled flows in the OLED.

A gate electrode G7 of the bypass transistor T7 is connected with the bypass control line 128, and a source electrode S7 of the bypass transistor T7 is connected with the drain electrode D6 of the light emission control transistor T6 and the anode of the OLED. A drain electrode D7 of the bypass transistor T7 is connected with the initialization voltage line 124 and the source electrode S4 of the initialization transistor T4.

The other end Cst2 of the storage capacitor Cst is connected with the driving voltage line 172, and a cathode of the OLED is connected with the common voltage ELVSS. The OLED receives the light emission current Ioled from the driving transistor T1 to emit light.

Next, an operation process of one pixel will be described.

First, for an initializing period, the previous scan signal Sn-1 having a low level is supplied through the previous scan line 122. Then, the initialization transistor T4 is turned on in response to the previous scan signal Sn-1 having the low level, the initialization voltage Vint is transferred from the initialization voltage line 124 to the gate electrode G1 of the driving transistor T1 through the initialization transistor T4, and the driving transistor T1 is initialized by the initialization voltage Vint.

Thereafter, for a data programming period, the scan signal Sn having the low level is supplied through the scan line 121. Then, the switching transistor T2 and the compensation transistor T3 are turned on in response to the scan signal Sn having the low level. In this case, the driving transistor T1 is diode-connected by the turned-on compensation transistor T3 and biased in a forward direction. Then, a compensation

voltage $Dm+V_{th}$ (V_{th} has a negative (-) value) reduced from the data signal Dm supplied from the data line 171 by a threshold voltage V_{th} of the driving transistor T1 is applied to the gate electrode G1 of the driving transistor T1.

The driving voltage ELVDD and the compensation voltage $Dm+V_{th}$ are applied to both ends of the storage capacitor Cst, and a charge corresponding to a voltage difference between both ends is stored in the storage capacitor Cst. Thereafter, for a light emission period, the light emission control signal En supplied from the light emission control line 123 is changed from a high level to a low level. Then, for the light emission period, the operation control transistor T5 and the light emission control transistor T6 are turned on by the light emission control signal En of the low level.

Then, a driving current Id is generated in substantial proportion to a voltage difference between the voltage of the gate electrode G1 of the driving transistor T1 and the driving voltage ELVDD, and the driving current Id is supplied to the OLED through the light emission control transistor T6. For the light emission period, a gate-source voltage Vgs of the driving transistor T1 is maintained as ' $(Dm+V_{th})-ELVDD$ ' by the storage capacitor Cst. According to a current-voltage relationship of the driving transistor T1, the driving current Id is proportional to ' $(Dm-ELVDD)^2$ ' which is a square of a value obtained by subtracting the threshold voltage V_{th} from the gate-source voltage Vgs. Accordingly, the driving current Id is determined regardless of the threshold voltage V_{th} of the driving transistor T1.

In this case, the bypass transistor T7 receives the bypass signal BP from the bypass control line 128. The bypass signal BP is a predetermined level of voltage which may always turn off the bypass transistor T7. As the gate electrode G7 of the bypass transistor T7 receives the voltage at the transistor off level, the bypass transistor T7 can be always turned off and a part of the driving current Id can be removed as the bypass current Ibp through the bypass transistor T7 in the off state.

Accordingly, when the driving current displaying a black image flows, the light emission current holed of the OLED is reduced by a current amount of the bypass current Ibp removed from the driving current Id through the bypass transistor T7 to become a minimum current amount as a level which may accurately express the black image. Therefore, a black luminance image is exactly implemented by using the bypass transistor T7 to improve a contrast ratio of the screen.

Next, a layout structure of a plurality of pixels will be described.

FIG. 4 is a schematic layout view of a plurality of pixels of the OLED display according to the exemplary embodiment.

Referring to FIG. 4, a plurality of green pixels G is disposed at intervals therebetween in a first row 1N, and red pixels R and blue pixels B are alternately disposed in a second row 2N. The green pixels G is disposed at intervals therebetween in a third row 3N, and the blue pixels B and the red pixels R are alternately disposed in a fourth row 4N. The layout of the pixels is repeated up to an N-th row.

The green pixels G disposed in the first row 1N and the red pixels R and the blue pixels B in the second row 2N are alternately positioned. Accordingly, in a first column 1M, red pixels R and blue pixels B are alternately disposed, and in a second column 2M, a plurality of green pixels G is disposed at intervals therebetween. In a third column 3M, blue pixels B and red pixels R are alternately disposed, and in a fourth column 4M, a plurality of green pixels G is

disposed at intervals therebetween. The layout of the pixels is repeated up to an M-th column.

Next, a detailed structure of the pixels illustrated in FIG. 3 will be described.

FIG. 5 is a schematic plan view illustrating a plurality of transistors and a plurality of signal lines of the OLED display according to the exemplary embodiment.

Referring to FIG. 5, the scan line 121 applying the scan signal Sn, the previous scan line 122 applying the previous scan signal Sn-1, the light emission control line 123 applying the light emission control signal En, and the bypass control line 128 applying the bypass signal BP may be formed in parallel to a row direction. The data line 171 applying the data signal Dm and the driving voltage line 172 applying the driving voltage ELVDD may be formed in parallel with a column direction. The initialization voltage line 124 applying the initialization voltage Vint is formed substantially in parallel with the row direction, but may include a portion crossing the scan line 121.

Further, in the pixel, the driving transistor T1, the switching transistor T2, the compensation transistor T3, the initialization transistor T4, the operation control transistor T5, the light emission control transistor T6, the bypass transistor T7, the storage capacitor Cst, and the OLED are formed.

The driving transistor T1, the switching transistor T2, the compensation transistor T3, the initialization transistor T4, the operation control transistor T5, the light emission control transistor T6, and the bypass transistor T7 are formed along the semiconductor layer 131. The semiconductor layer 131 may be curved in various shapes and formed by polysilicon or oxide semiconductors. When the semiconductor layer 131 includes the oxide semiconductor, a separate passivation layer for protecting the semiconductor layer may be added.

FIG. 6 is a detailed layout view of FIG. 5, and FIG. 7 is a cross-sectional view taken along line VII-VII' of FIG. 6. FIG. 8 is a cross-sectional view taken along lines VIII-VIII' and VIII'-VIII" of FIG. 6, and FIG. 9 is a cross-sectional view taken along line IX-IX' of FIG. 6.

Referring to FIGS. 5 to 9, the semiconductor layer 131 includes a driving semiconductor layer 131a formed in the driving transistor T1, a switching semiconductor layer 131b formed in the switching transistor T2, a compensation semiconductor layer 131c formed in the compensation transistor T3, an initialization semiconductor layer 131d formed in the initialization transistor T4, an operation control semiconductor layer 131e formed in the operation control transistor T5, a light emission control semiconductor layer 131f formed in the light emission control transistor T6, and a bypass semiconductor layer 131g formed in the bypass transistor T7.

The driving transistor T1 includes the driving semiconductor layer 131a, a driving gate electrode 125a, a driving source electrode 176a, and a driving drain electrode 177d. The driving semiconductor layer 131a is curved and may have an oblique shape or a zigzag shape. In this case, the driving semiconductor layer 131a may be elongated in a narrow space and a driving channel region 131a1 of the driving semiconductor layer 131a has a large length to widen a driving range of the gate voltage applied to the driving gate electrode 125a. Accordingly, a magnitude of the gate voltage is changed to more finely control a gray scale of the light emitted from the OLED.

The driving source electrode 176a and the driving drain electrode 177a correspond to a driving source region 176a and a driving drain region 177a which are doped with impurities in the driving semiconductor layer 131a, respectively. For convenience, the same reference numerals are

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applied to the electrode and the region. The driving gate electrode **125a** at least partially overlaps the driving semiconductor layer **131a**, and may be formed on the same layer with the same material as the scan line **121**, the previous scan line **122**, the light emission control line **123**, a switching gate electrode **125b**, a compensation gate electrode **125c**, an initialization gate electrode **125d**, an operation control gate electrode **125e**, and a light emission control gate electrode **125f**.

The switching transistor **T2** includes the switching semiconductor layer **131b**, a switching gate electrode **125b**, a switching source electrode **176b**, and a switching drain electrode **177b**. The switching gate electrode **125b** is a part of the scan line **121**. In a part of the data line **171**, the switching source electrode **176b** is connected with the switching source region **132b** which is doped with an impurity in the switching semiconductor layer **131b**, and the switching drain electrode **177b** corresponds to the switching drain region **177b** which is doped with an impurity in the switching semiconductor layer **131b**.

The compensation transistor **T3** includes a compensation semiconductor layer **131c**, a compensation gate electrode **125c**, a compensation source electrode **176c**, and a compensation drain electrode **177c**. The compensation source electrode **176c** and the compensation drain electrode **177c** correspond to the compensation source region **176c** and the compensation drain region **177c** which are doped with impurity in the compensation semiconductor layer **131c**, respectively.

The initialization transistor **T4** includes the initialization semiconductor layer **131d**, an initialization gate electrode **125d**, an initialization source electrode **176d**, and an initialization drain electrode **177d**. The initialization drain electrode **177d** corresponds to the initialization drain region **177d** which is doped with an impurity in the initialization semiconductor layer **131d**. The initialization source electrode **176d** is connected through a contact hole **64** with the initialization source region **132d** which is doped with an impurity in the initialization semiconductor layer **131d**. The initialization voltage line **124** is connected with the initialization source electrode **176d** through a contact hole **82** and connected with the initialization semiconductor layer **131d** through the initialization source electrode **176d**.

The operation control transistor **T5** includes the operation control semiconductor layer **131e**, an operation control gate electrode **125e**, an operation control source electrode **176e**, and an operation control drain electrode **177e**. The operation control source electrode **176e** which is a part of the driving voltage line **172** is connected with the operation control semiconductor layer **131e**, and the operation control drain electrode **177e** corresponds to an operation control drain region **177e** which is doped with an impurity in the operation control semiconductor layer **131e**.

The light emission control transistor **T6** includes the light emission control semiconductor layer **131f**, a light emission control gate electrode **125f**, a light emission control source electrode **176f**, and a light emission control drain electrode **177f**. The light emission control source electrode **176f** corresponds to the light emission control source region **176f** which is doped with an impurity in the light emission control semiconductor layer **131f**, and the light emission control drain electrode **177f** is connected with the light emission control drain region **133f** of the light emission control semiconductor layer **131f**.

The bypass transistor **T7** includes the bypass semiconductor layer **131g**, a bypass gate electrode **125g**, a bypass source electrode **176g**, and a bypass drain electrode **177g**.

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The bypass source electrode **176g** and the bypass drain electrode **177g** correspond to a bypass source region **176g** and a bypass drain region **177g** which are doped with impurities in the bypass semiconductor layer **131g**, respectively. The bypass source electrode **176g** is directly connected with the light emission control drain region **133f**.

One end of the driving semiconductor layer **131a** is connected with the switching semiconductor layer **131b** and the operation control semiconductor layer **131e**, and the other end of the driving semiconductor layer **131a** is connected with the compensation semiconductor layer **131c** and the light emission control semiconductor layer **131f**. Accordingly, the driving source electrode **176a** is connected with the switching drain electrode **177b** and the operation control drain electrode **177e**, and the driving drain electrode **177a** is connected with the compensation source electrode **176c** and the light emission control source electrode **176f**.

The storage capacitor **Cst** includes a first storage capacitor plate and a second storage capacitor plate **126** which are disposed with the second gate insulating layer **142** therebetween. The driving gate electrode **125a** becomes the first storage capacitor plate, and the second gate insulating layer **142** becomes a dielectric material. A storage capacitance is determined by charges stored in the storage capacitor **Cst** and a voltage between both capacitor plates **125a** and **126**.

A connecting member **174** is substantially parallel with the data line **171** and formed on the same layer as the data line **171**. The connecting member **174** is connected to the first storage capacitor plate (driving gate electrode) **125a** at one end and connected with the compensation drain electrode **177c** at the other end to connect the driving gate electrode **125a** and the compensation drain electrode **177c**. Accordingly, the storage capacitor **Cst** may store a storage capacitance corresponding to a difference between the driving voltage **ELVDD** transferred to the second storage capacitor plate **126** through the driving voltage line **172** and the gate voltage of the driving gate electrode **125a**.

The switching transistor **T2** is used as a switching element selecting a pixel to emit light. The switching gate electrode **125b** is connected to the scan line **121**, the switching source electrode **176b** is connected to the data line **171**, and the switching drain electrode **177b** is connected with the driving transistor **T1** and the operation control transistor **T5**. The light emission control drain electrode **177f** of the light emission control transistor **T6** is directly connected with the pixel electrode (anode) **191** of the OLED.

The connecting member **174** may be positioned with a planar distance **d** from the pixel electrode **191** (see FIG. 5). In this case, since the connecting member **174** does not overlap the pixel electrode **191**, a parasitic capacitor between the connecting member **174** and the pixel electrode **191** is not generated.

Accordingly, since the OLED is not influenced by a voltage change of the connecting member **174**, an amplitude of the driving current **Id** flowing in the OLED is almost not changed even in the case where a common voltage **ELVSS** is changed. As a result, luminance and a color of the OLED may be substantially uniformly maintained, and the common voltage **ELVSS** is changed by using the feature to lower power consumption.

Next, a structure in a laminated order will be described with reference to FIGS. 7 to 9. In this case, since a laminated structure of the operation control transistor **T5** is almost the same as that of the light emission control transistor **T6**, a detailed description thereof is omitted.

The buffer layer **120** is formed on the substrate **110**. In addition, on the buffer layer **120**, the driving semiconductor

layer **131a**, the switching semiconductor layer **131b**, the compensation semiconductor layer **131c**, the initialization semiconductor layer **131d**, the operation control semiconductor layer **131e**, the light emission control semiconductor layer **131f**, and the bypass semiconductor layer **131g** are formed.

The driving semiconductor layer **131a** includes a driving channel region **131a1**, a driving source region **176a**, and a driving drain region **177a**. The switching semiconductor layer **131b** includes a switching channel region **131b1**, a switching source region **132b**, and a switching drain region **177b**. The compensation semiconductor layer **131c** includes a compensation channel region **131c**, a compensation source region **176c**, and a compensation drain region **177c**. For convenience, the same reference numerals are applied to the semiconductor layer and the channel region.

The initialization semiconductor layer **131d** includes an initialization channel region **131d1**, an initialization source region **132d**, and an initialization drain region **177d**. The light emission control semiconductor layer **131f** includes a light emission control channel region **131f1**, a light emission control source region **176f**, and a light emission control drain region **133f**. The bypass semiconductor layer **131g** includes a bypass channel region **131g**, a bypass source region **176g**, and a bypass drain region **177g**.

On the driving semiconductor layer **131a**, the switching semiconductor layer **131b**, the compensation semiconductor layer **131c**, the initialization semiconductor layer **131d**, the operation control semiconductor layer **131e**, the light emission control semiconductor layer **131f**, and the bypass semiconductor layer **131g**, the first gate insulating layer **141** is formed. On the first gate insulating layer **141**, a gate wire including the scan line **121**, the previous scan line **122**, the light emission control line **123**, and the bypass control line **128** is formed.

The scan line **121** includes a switching gate electrode **125b** and a compensation gate electrode **125c**, and the previous scan line **122** includes an initialization gate electrode **125d**. The light emission control line **123** includes an operation control gate electrode **125e** and a light emission control gate electrode **125f**, and the bypass control line **128** includes a driving gate electrode (first storage capacitor plate) **125a** and a bypass gate electrode **125g**. On the gate wire and the first gate insulating layer **141**, the second gate insulating layer **142** is formed.

On the second gate insulating layer **142**, the second storage capacitor plate **126** overlapping with the storage capacitor plate **125a** is formed. The second storage capacitor plate **126** is wider than the first storage capacitor plate **125a** to entirely cover the driving gate electrode **125a**. Accordingly, the second storage capacitor plate **126** may block a voltage change of the driving gate electrode **125a** from being influenced by the voltage of the pixel electrode **191** overlapping with the driving gate electrode **125a**.

On the second gate insulating layer **142** and the second storage capacitor plate **126**, the interlayer insulating layer **160** is formed. A data wire is formed on the interlayer insulating layer **160**. The data wire includes a data line **171** including a switching source electrode **176b**, a driving voltage line **172**, a connecting member **174**, an initialization source electrode **176d**, and a light emission control drain electrode **177f**.

The switching source electrode **176b** is connected with the switching source region **132b** through a contact hole **62** formed in the first and second gate insulating layer **141** and **142** and the interlayer insulating layer **160**, and the driving voltage line **172** is connected with second storage capacitor

plate **126** through a contact hole **67** formed in the interlayer insulating layer **160**. The driving voltage line **172** is connected with the operation control source electrode **176e** through a contact hole **65** formed in the first and second gate insulating layers **141** and **142**.

One end of the connecting member **174** is connected with the driving gate electrode **125a** through a contact hole **61** formed in the second gate insulating layer **142** and the interlayer insulating layer **160**, and the other end of the connecting member **174** is connected with the compensation drain electrode **177c** through a contact hole **63** formed in the first and second gate insulating layers **141** and **142** and the interlayer insulating layer **160**. In this case, one end of the connecting member **174** is positioned in a capacitor groove **68** formed on the second storage capacitor plate **126**.

The initialization source electrode **176d** is connected with the initialization semiconductor layer **131d** through a contact hole **64** formed in the first and second gate insulating layers **141** and **142** and the interlayer insulating layer **160**. The light emission control drain electrode **177f** is connected with the light emission control semiconductor layer **131f** through a contact hole **66** formed in the first and second gate insulating layers **141** and **142** and the interlayer insulating layer **160**.

The passivation layer **180** covering the data wire is formed on the interlayer insulating layer **160**, and the pixel electrode **191** and the initialization voltage line **124** are formed on the passivation layer **180**. The light emission control drain electrode **177f** is connected with an extension **191b** of the pixel electrode **191** through a contact hole **81** formed in the passivation layer **180**, and the initialization source electrode **176d** is connected with the initialization voltage line **124** through a contact hole **82** formed in the passivation layer **180**.

A partition wall **350** is formed on the edge of the pixel electrode **191** and the passivation layer **180**. The partition wall **350** forms an opening **351** exposing the pixel electrode **191**. The passivation layer **180** and the partition wall **350** may be made of organic materials such as a polyacryl-based resin or a polyimide-based resin. The organic emission layer **370** is formed on the pixel electrode **191** exposed by the opening **351**, and the common electrode **270** is formed on the organic emission layer **370**.

A red organic emission layer, a green organic emission layer, and a blue organic emission layer may be formed in a red pixel R, a green pixel G, and a blue pixel B illustrated in FIG. 4, respectively. On the other hand, the red organic emission layer, the green organic emission layer, and the blue organic emission layer are laminated on all of the red pixel R, the green pixel G, and the blue pixel B, and a red filter, a green filter, and a blue filter may be formed in the red pixel R, the green pixel G, and the blue pixel B, respectively.

On the other hand, white organic emission layers are laminated on all of the red pixel R, the green pixel G, and the blue pixel B, and a red filter, a green filter, and a blue filter may be formed in the red pixel R, the green pixel G, and the blue pixel B, respectively. For example, the white organic emission layers may include a yellow organic emission layer and a blue organic emission layer, include a cyan organic emission layer and a red organic emission layer, or include a magenta organic emission layer and a green organic emission layer.

An encapsulation member (not illustrated) sealing the OLED is formed on the common electrode **270**. The encapsulation member may be sealed on the substrate **110** by a sealant or configured by a thin film encapsulation formed by laminating an inorganic film and an organic film on the common electrode **270**.

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In FIG. 4, the red pixel R, the green pixel G, and the blue pixel B may have the same shape as the pixel electrode 191 of the corresponding pixel. That is, hereinabove, the planar shape of the pixel electrode 191 is assumed as the shape of the corresponding pixel. The pixel electrode 191 includes an edge which is formed to be larger than the organic emission layer 370 and does not overlap with the organic emission layer 370, and includes an extension 191b overlapping with a contact hole 81. The initialization voltage line 124 may be positioned between the pixels in the second row 2N and the pixels in the third row 3N and formed by a repeated curved pattern.

The pixel electrode 191 includes a first curved portion 191a which is concavely or convexly formed in a region which does not overlap with the organic emission layer 370, that is, an edge of the pixel electrode 191. The first curved portion 191a does not directly reflect light (external light) incident from the environment but scatters the light to minimize the reflection of the external light. The initialization voltage line 124 also includes a second curved portion 124a formed concavely or convexly toward the common electrode 270 to scatter the external light. In this case, the initialization voltage line 124 may include a second curved portion 124a formed at the remaining portion except for the portion overlapping with the contact hole 82.

In FIGS. 7 to 9, the case where the surface of the passivation layer 180 includes the concave portions 180a and the first curved portion 191a and the second curved portion 124a are concavely formed is illustrated as an example. Meanwhile, the surface of the passivation layer 180 may include a plurality of convex portions, and the first curved portion and the second curved portion may be convexly formed.

While the inventive technology has been described in connection with what is presently considered to be practical exemplary embodiments, it is to be understood that the invention is not limited to the disclosed embodiments, but, on the contrary, is intended to cover various modifications and equivalent arrangements included within the spirit and scope of the appended claims.

What is claimed is:

1. An organic light emitting diode (OLED) display, comprising:

a substrate;
a plurality of transistors over the substrate;
a passivation layer covering the transistors; and
an OLED over the passivation layer and including a pixel electrode, an organic emission layer, and a common electrode,
wherein the pixel electrode includes a first curved portion that does not overlap the organic emission layer in the direction of light emission.

2. The OLED display of claim 1, wherein the pixel electrode includes a metal reflective film, and wherein the common electrode includes at least one of a transparent conductive film and a translucent conductive film.

3. The OLED display of claim 2, further comprising:
an initialization voltage line over the passivation layer and of the same material as the pixel electrode,
wherein the initialization voltage line includes a second curved portion.

4. The OLED display of claim 3, wherein the first and second curved portions have substantially the same shape.

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5. The OLED display of claim 3, wherein the first and second curved portions have substantially the same size.

6. The OLED display of claim 3, wherein the first and second curved portions do not directly contact each other.

7. The OLED display of claim 3, wherein the second curved portions is not directly above the transistors.

8. The OLED display of claim 3, wherein the first and second curved portions are concave toward the common electrode.

9. The OLED display of claim 8, wherein the surface of the passivation layer includes a plurality of concave portions, and wherein the first and second curved portions are over the concave portions with predetermined thicknesses.

10. The OLED display of claim 3, wherein the first and second curved portions are convex toward the common electrode.

11. The OLED display of claim 10, wherein the surface of the passivation layer includes a plurality of convex portions, and wherein the first and second curved portions are over the convex portions with predetermined thicknesses.

12. The OLED display of claim 3, wherein the second curved portion is at the remaining portion except for the portion overlapping the contact hole of the initialization voltage line.

13. The OLED display of claim 1, wherein the first curved portion is not directly below the organic emission layer.

14. The OLED display of claim 1, wherein each of the transistors includes source and drain electrodes, wherein the pixel electrode includes a non-linear portion that contacts one of the source and drain electrodes, and wherein the height of the first curved portion is similar to that of the non-linear portion.

15. The OLED display of claim 1, wherein the passivation layer has a groove or protrusion on which the first curved portion is located.

16. An organic light emitting diode (OLED) display, comprising:

a substrate;
a plurality of transistors over the substrate;
a passivation layer covering the transistors; and
a plurality of OLEDs over the passivation layer, wherein each of the OLEDs includes a pixel electrode, an organic emission layer, and a common electrode,
wherein the pixel electrode includes at least one first curved portion that is convex or concave with respect to the common electrode, and wherein the first curved portion is between adjacent organic emission layers, and wherein the first curved portion is not directly above any of the transistors.

17. The OLED display of claim 16, wherein the first curved portion does not overlap the organic emission layer in the depth dimension of the OLED display.

18. The OLED display of claim 16, further comprising an initialization voltage line over the passivation layer, wherein the initialization voltage line includes at least one second curved portion that is convex or concave with respect to the common electrode.

19. The OLED display of claim 16, wherein the passivation layer has a groove or protrusion on which the first curved portion is located.

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专利名称(译)	有机发光二极管显示器		
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[标]申请(专利权)人(译)	三星显示有限公司		
申请(专利权)人(译)	三星DISPLAY CO. , LTD.		
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摘要(译)

公开了一种有机发光二极管 (OLED) 显示器。在一个方面, OLED显示器包括衬底, 在衬底上形成的多个晶体管和覆盖晶体管的钝化层。OLED显示器还包括形成在钝化层上并包括像素电极, 有机发射层和公共电极的OLED。像素电极包括在OLED显示器的深度维度上不与有机发射层重叠的第一弯曲部分。

